

/ Descriptions

KF \$))' GE G Silicon PNP transistor in a TO-220 Plastic Package.

/ Features

\$ D A< , ' * /
High DC current gain, High V_{CE0} , High f_T , Complementary pair with MJE15036.

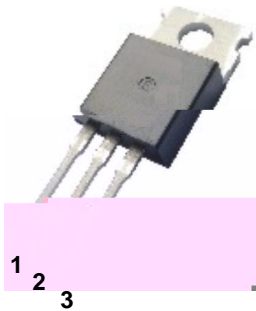
/ Applications

Designed for us as high-frequency drivers in audio amplifiers.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

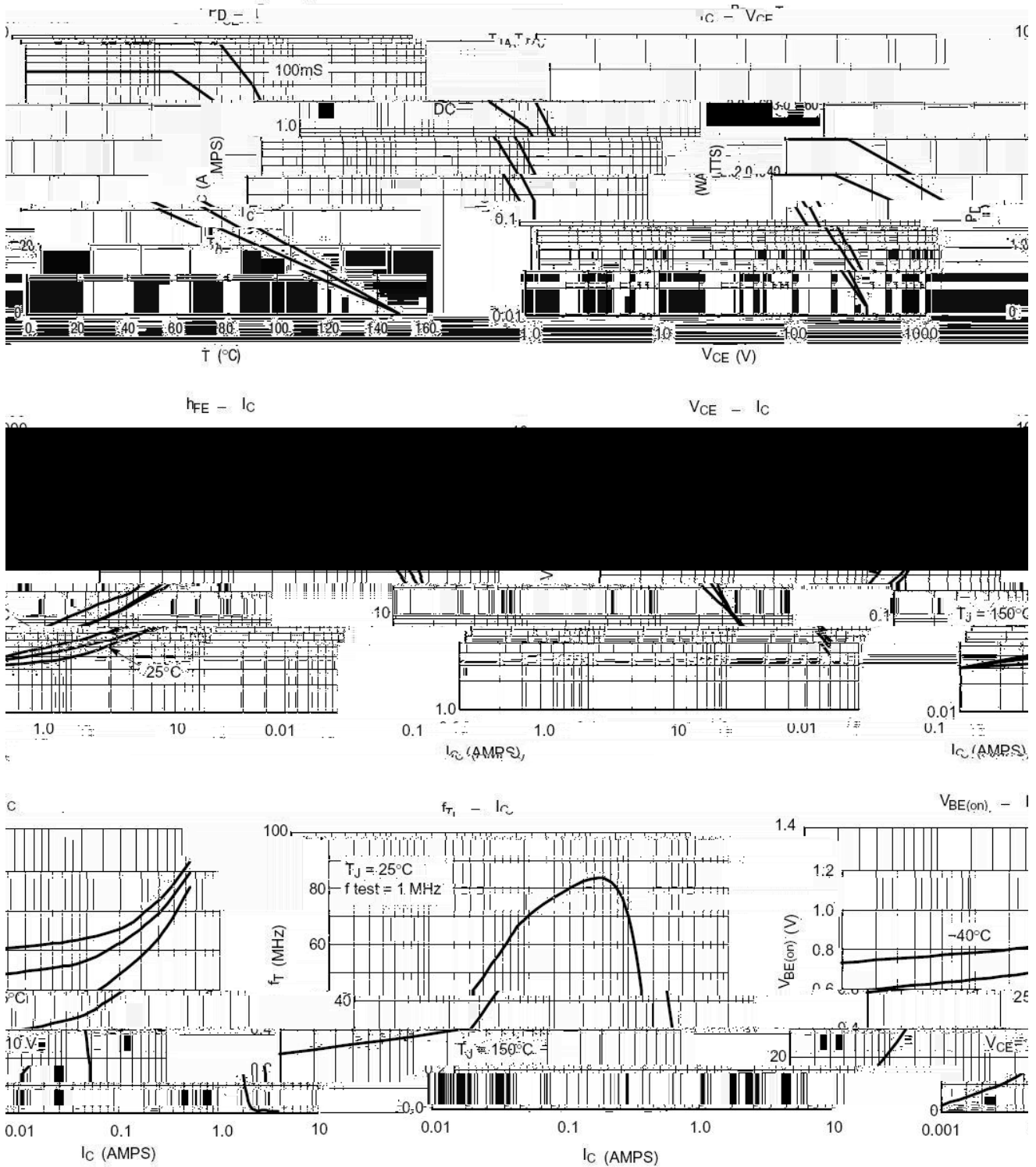
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-350	V
Collector to Emitter Voltage	V_{CEO}	-350	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-8	A
Base Current - Continuous	I_B	-2	A
Collector Power Dissipation	P_D	2	W
	$P_D(T_C=25)$	80	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	
Thermal Resistance, Junction to Case	R_{JC}	2.5	/W
Thermal Resistance, Junction to Ambient	R_{JA}	62.5	/W

/ Electrical Characteristics(Ta=25)

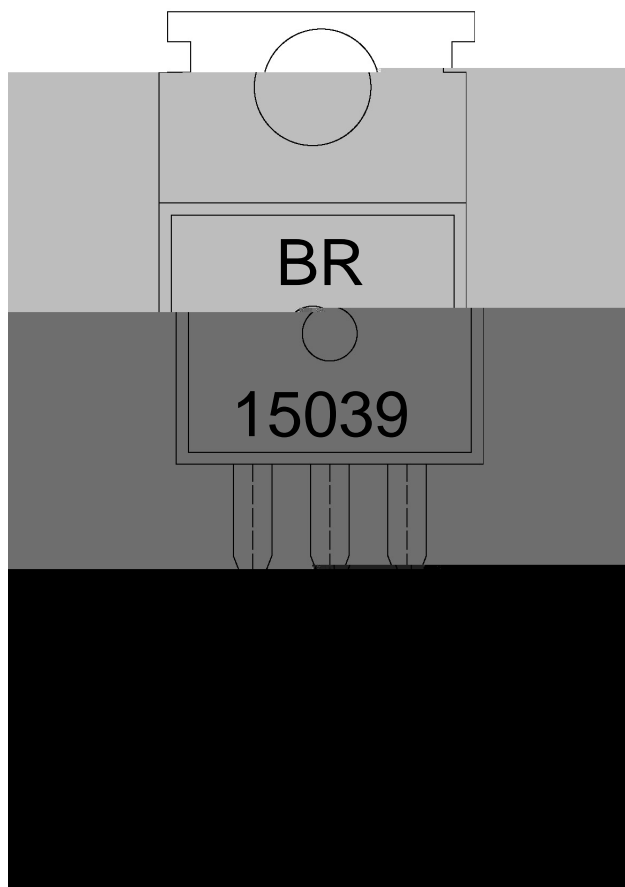
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	* V_{CEO}	$I_C=-10mA$ $I_B=0$	-350			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-350V$ $I_E=0$			-30	μA
Emitter Cut-Off Current	I_{EBO}	$V_{BE}=-5V$ $I_C=0$			-30	μA
DC Current Gain	* $h_{FE(1)}$	$V_{CE}=-5V$ $I_C=-0.5A$	100		500	
	* $h_{FE(2)}$	$V_{CE}=-5V$ $I_C=-0.1A$	100			
	* $h_{FE(3)}$	$V_{CE}=-5V$ $I_C=-1A$	5			
	$h_{FE(4)}$	$V_{CE}=-5V$ $I_C=-2A$	10			
Collector to Emitter Saturation Voltage	* $V_{CE(sat)}$	$I_C=-1A$ $I_B=0.1A$			-0.5	V
Base to Emitter On Voltage	* $V_{BE(on)}$	$V_{CE}=5V$ $I_C=-1A$			-1	V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_C=-500mA$ $f=1MHz$	30			MHz

! *' ' μj) fl *Pulse Test: Pulse Width 300 μs , Duty Cycle 2%.

/ Electrical Characteristic Curve



/ Marking Instructions



BR

15039

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Note:

BR: Company Code

15039: Product Type.

****: Lot No. Code, code change with Lot No.

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